

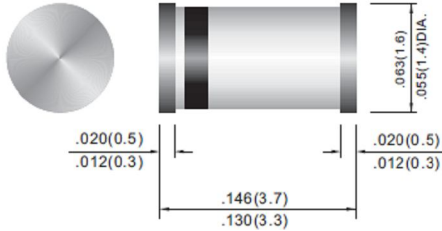


# BAV101 THRU BAV103

## High Voltage Surface Mount Switching Diodes

Voltage 120 to 250 volts Power 300 mwatts

### MINI-MELF/LL-34



Unit: inch(mm)

### FEATURES

- ◆ Fast switching speed
- ◆ Surface mount package ideally suited for automatic insertion
- ◆ Silicon epitaxial planar construction
- ◆ Both normal and Pb free product are available:  
Normal:80~95% Sn, 5~20% Pb  
Pb free:98.5% Sn above

### MECHANICAL DATA

**Case:** Mini Melf, Glass

**Terminals:** Solderable per MIL-STD-202E, method 208

**Approx:** Weight:0.03 gram

**Polarity:** Cathode band

**Marking:** Cathode band only

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

T<sub>J</sub>=25°C unless otherwise noted

PARAMETR	SYMBOLS	BAV101	BAV102	BAV103	UNITS
Reverse Voltage	V <sub>R</sub>	100	150	200	Volts
Peak Reverse Voltage	V <sub>RM</sub>	120	200	250	Volts
Rectified Current(Average), Half Wave Rectification with Resistive Load and f>=50Hz	I <sub>o</sub>	200			mAmps
Peak forward surge current, t=1.0s	I <sub>FSM</sub>	1.0			Amps
Power Dissipation Derate Above at 25°C	P <sub>D</sub>	300			mWatts
Maximum Forward Voltage, I <sub>F</sub> =100mA	V <sub>R</sub>	1.0			Volts
Maximum DC Reverse Current at Rated DC Blocking Voltage T <sub>J</sub> =25°C	I <sub>R</sub>	0.1			uA
Typical junction capacitance (NOTE 1)	C <sub>J</sub>	0.95			pF
Maximum Reverse Recovery (NOTE 2)	T <sub>RR</sub>	75			ns
Maximum Thermal Resistance	R <sub>ΘJA</sub>	350			°C/W
Operation Junction Storage Temperature Range	T <sub>STG</sub>	-65 to +125			°C

NOTES:

1.C<sub>J</sub>at V<sub>R</sub>=0,f=1MHZ .

2.From I<sub>F</sub>=10mA to I<sub>R</sub>=1mA, V<sub>R</sub>=6 volts, R<sub>L</sub>=100Ω

# RATINGS AND CHARACTERISTIC CURVES

Fig.1 Forward Characteristics

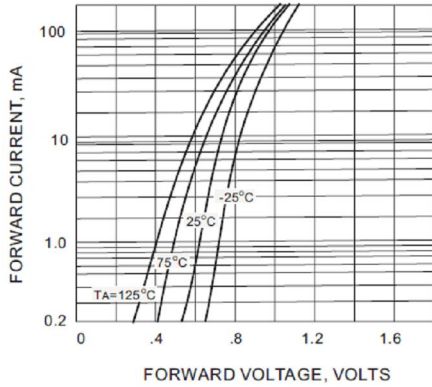


Fig.2 Typical Capacitance vs Reverse Voltage

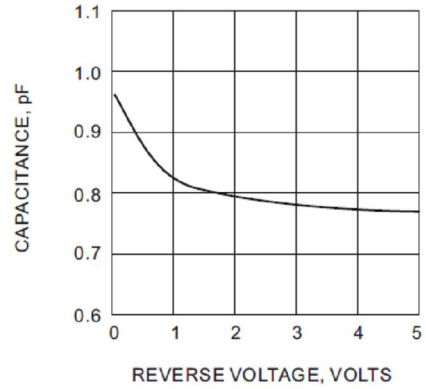


Fig.3 Surge Current Characteristic

